I hereby certify that this correspondence is being deposited with the united states postal service as in an envelope addressed to: Commissioner of Patents, P.O.Box 1450, Alexandria, VA 22313, on August 12, 2003. The applicant and/or attorney requests the date of deposit as the filing date.

Depositor: Karen Cing-Mars

ignature & date)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of ____:

August 12, 2003

Hendrik F. Hamann et al. :

Group Art Unit:

Serial No. 10/604,486

Examiner:

Filed: 07/25/2003

International Business Machines Corporation

2070 Route 52

Hopewell Junction, NY 12533

<u>TITLE:</u> SYSTEM AND METHOD OF ALTERING A VERY SMALL SURFACE AREA BY MULTIPLE CHANNEL PROBE

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents P.O. Box 1450 Alexandria, Virginia 22313-1450

Sir:

Pursuant to the duty of disclosure set forth in 37 C.F.R. 1.56, and further pursuant to the provisions of 37 C.F.R. 1.97 and 1.98, applicants hereby respectfully submit copies of the prior patents and publications as listed on Form PTO-1449, attached hereto.

In citing these documents, no representation is made nor intended as to the pertinency or non-pertinency of the art, that better art than that listed is not available, or that other art is not applicable.

Respectfully submitted, Hendrik F. Hamann et al.

BY

Steven Capella, Attorney Registration No. 33,086

Telephone No. 845-894-3669

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